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INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 4

Complete if Known	
Application Number	10/695,419-Conf. #4483
Filing Date	October 27, 2003
First Named Inventor	LinLin Chen
Art Unit	~~2848~~ 1745
Examiner Name	~~P. T. Dang~~ T. Parsons
Attorney Docket Number	291958171US4

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.[1]	Document Number Number-Kind Code[2] (If known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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Examiner Signature	Thomas H. Parsons	Date Considered	8/26/2004

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Sheet 2 of 4

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Application Number	10/695,419-Conf. #4483
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Art Unit	~~2818~~ 1745
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NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.[1]	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T[2]
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Examiner Signature	Thomas H. Parsons	Date Considered	8/26/2004

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Sheet 3 of 4

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Examiner Name	~~P. T. Dang~~ T. Parsons
Attorney Docket Number	291958171US4

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Examiner Signature	Thomas H. Parsons	Date Considered	8/26/2004

* No month and/or year provided

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[1]Applicant's unique citation designation number (optional). [2]Applicant is to place a check mark here if English language Translation is attached.

Examiner Signature	Thomas H. Parsons	Date Considered	8/26/2004

* No month and/or year provided